AlGaAs laser diodes RLD-78MC

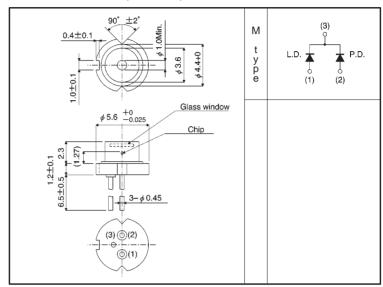
The RLD-78MC is the world's first mass-produced laser diodes that is manufactured by molecular beam epitaxy. The characteristics of this laser diode are suitable for use in sensors and bar code readers.

ApplicationsSensorsBar code readersMeasuring instruments

Features

- 1) One-third the dispersion compared with conventional laser diodes.
- 2) High-precision, compact package.

External dimensions (Units: mm)



Note: The lengths of the RLD-78MC leads are 5.0 \pm 0.5 mm.

● Absolute maximum ratings (Tc = 25°C)

| Parameter | | Symbol | Limits | Unit |
|-----------------------|----------------|----------|----------------------|------|
| Output | | Po | 5 | mW |
| Reverse voltage | Laser | VR | 2 | V |
| | PIN photodiode | VR (PIN) | 30 | V |
| Operating temperature | | Topr | -10~ + 60 | °C |
| Storage temperature | | Tstg | -40~+85 | °C |

Laser diodes RLD-78MC

• Electrical and optical characteristics (Tc = 25°C)

| Parameter | Symbol | Min. | Тур. | Max. | Unit | Conditions |
|--------------------------------|----------------|------|------|------|-------|----------------------|
| Threshold current | Ith | - | 35 | 60 | mA | _ |
| Operating current | lop | - | 45 | 70 | mA | Po=3mW |
| Operating voltage | Vop | - | 1.9 | 2.3 | ٧ | Po=3mW |
| Differential efficiency | η | 0.1 | 0.25 | 0.6 | mW/mA | 2mW I(3mW)—I(1mW) |
| Monitor current | lm | 0.1 | 0.2 | 0.6 | mA | Po=3mW,VR(PIN)=15V |
| Parallel divergence angle | θ //* | 8 | 11 | 15 | deg | Po=3mW |
| Perpendicular divergence angle | θ ⊥* | 20 | 37 | 45 | deg | |
| Parallel deviation angle | Δ φ // | _ | _ | ±2 | deg | |
| Perpendicular deviation angle | Δ φ ⊥ | _ | _ | ±3 | deg | |
| Emission point accuracy | ΔX ΔΥ ΔΖ | _ | _ | ±80 | μm | - |
| Peak emission wavelength | λ | 770 | 785 | 810 | nm | Po=3mW |

^{*} θ // and θ \perp are defined as the angle within which the intensity is 50% of the peak value.

Electrical and optical characteristic curves

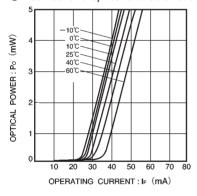


Fig. 1 Optical output vs. operating current

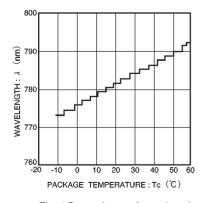


Fig. 4 Dependence of wavelength on temperature

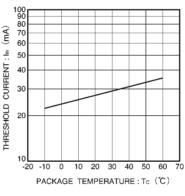


Fig. 2 Dependence of threshold current on temperature

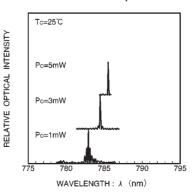


Fig. 5 Dependence of emission spectrum on optical output

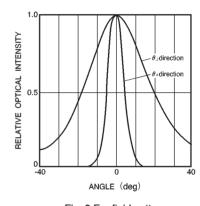


Fig. 3 Far field pattern

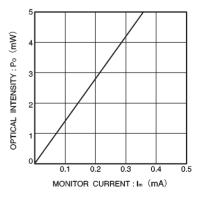


Fig. 6 Monitor current vs. optical output

